2.5V Drive Nch MOSFET

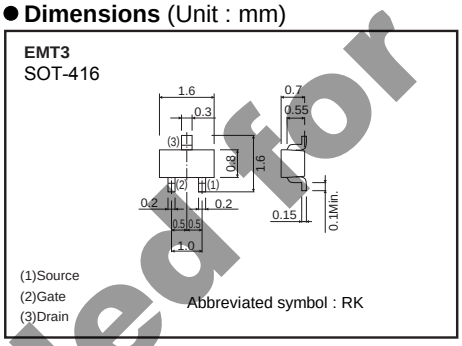
RSE002N06

● Structure
Silicon N-channel MOSFET

● Features
1) High speed switing.
2) Small package(EMT3).
3) Low voltage drive(2.5V drive).

● Application
Switching

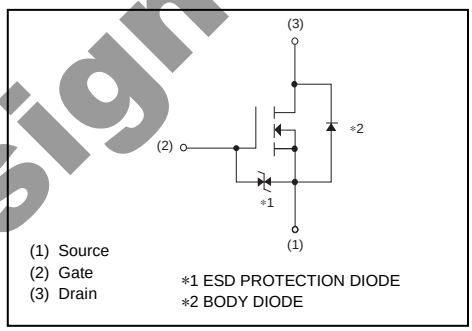
● Dimensions (Unit : mm)



● Packaging specifications

Type	Package	Taping
	Code	TL
	Basic ordering unit (pieces)	3000
RSE002N06		O

● Inner circuit



● Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		V_{DSS}	60	V
Gate-source voltage		V_{GSS}	±20	V
Drain current	Continuous	I_D	±250	mA
	Pulsed	I_{DP} *1	±1	A
Source current (Body Diode)	Continuous	I_S	125	mA
	Pulsed	I_{SP} *1	1	A
Power dissipation		P_D *2	150	mW
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	−55 to +150	°C

*1 Pw≤10μs, Duty cycle≤1%

*2 Each terminal mounted on a recommended land.

● Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth (ch-a)*	833	°C / W

* Each terminal mounted on a recommended land.

●**Electrical characteristics** (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	-	-	±10	μA	V_{GS}=±20V, V_{DS}=0V
Drain-source breakdown voltage	$V_{(BR)DSS}$	60	-	-	V	I_D=1mA, V_{GS}=0V
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	V_{DS}=60V, V_{GS}=0V
Gate threshold voltage	$V_{GS\ (th)}$	1.0	-	2.3	V	V_{DS}=10V, I_D=1mA
Static drain-source on-state resistance	$R_{DS\ (on)}$*	-	1.7	2.4	Ω	I_D=250mA, V_{GS}=10V
		-	2.1	3.0		I_D=250mA, V_{GS}=4.5V
		-	2.3	3.2		I_D=250mA, V_{GS}=4.0V
		-	3.0	12.0		I_D=10mA, V_{GS}=2.5V
Forward transfer admittance	$\|Y_{fs}\|$*	0.25	-	-	S	I_D=250mA, V_{DS}=10V
Input capacitance	C_{iss}	-	15	-	pF	V_{DS}=25V
Output capacitance	C_{oss}	-	4.5	-	pF	V_{GS}=0V
Reverse transfer capacitance	C_{rss}	-	2.0	-	pF	f=1MHz
Turn-on delay time	$t_{d(on)}$*	-	3.5	-	ns	I_D=100mA, V_{DD}≒ 30V
Rise time	t_r *	-	5	-	ns	V_{GS}=10V
Turn-off delay time	$t_{d(off)}$*	-	18	-	ns	R_L≒300Ω
Fall time	t_f *	-	28	-	ns	R_G=10Ω

*Pulsed

●**Body diode characteristics** (Source-Drain) (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{SD}*	-	-	1.2	V	I_S=250mA, V_{GS}=0V

*Pulsed

●Electrical characteristic curves

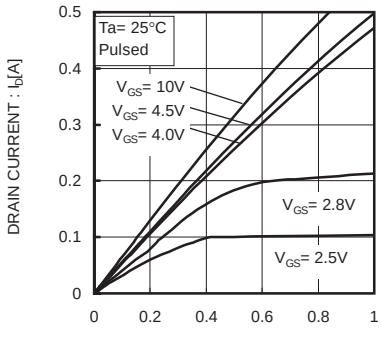


Fig.1 Typical Output Characteristics(I)

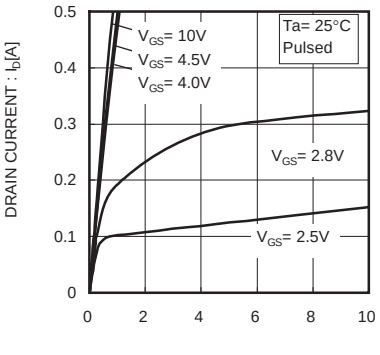


Fig.2 Typical Output Characteristics(II)

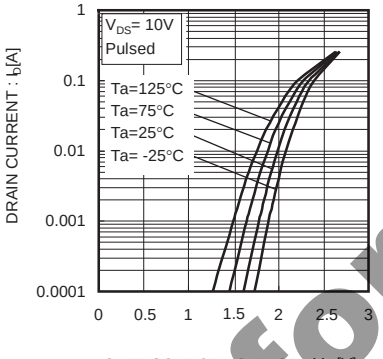


Fig.3 Typical Transfer Characteristics

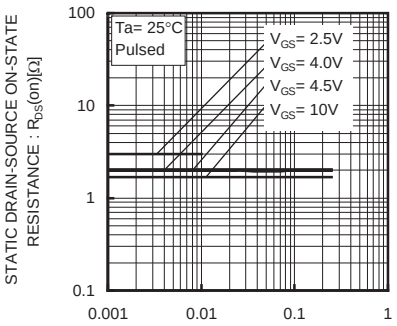


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current(I)

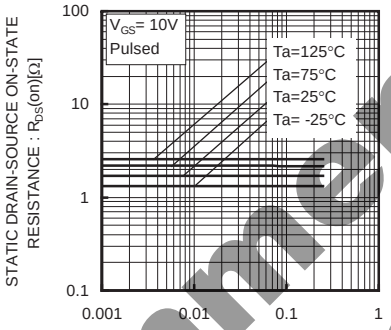


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current(II)

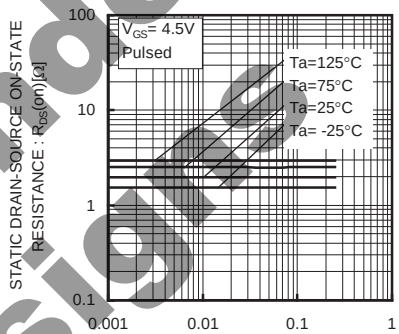


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current(III)

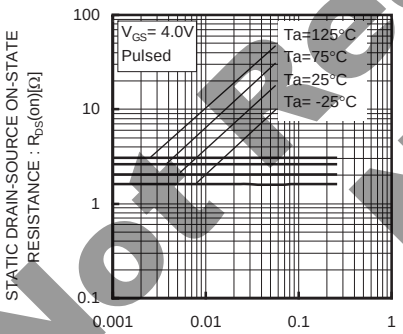


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current(IV)

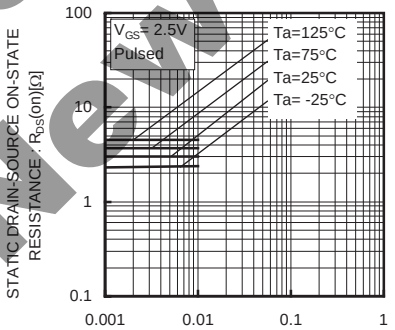


Fig.8 Static Drain-Source On-State Resistance vs. Drain Current(IV)

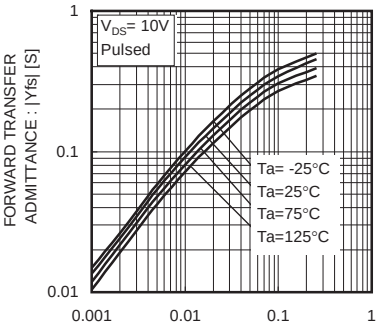


Fig.9 Forward Transfer Admittance vs. Drain Current

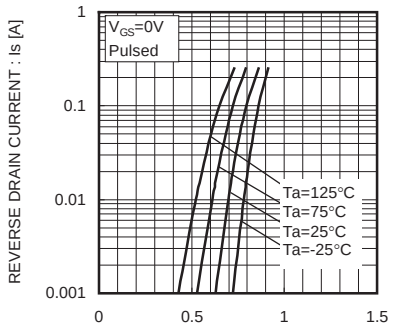


Fig.10 Reverse Drain Current vs. Sourse-Drain Voltage

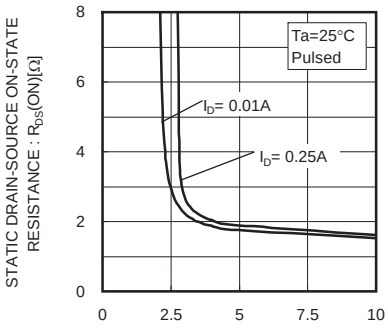


Fig.11 Static Drain-Source On-State Resistance vs. Gate Source Voltage

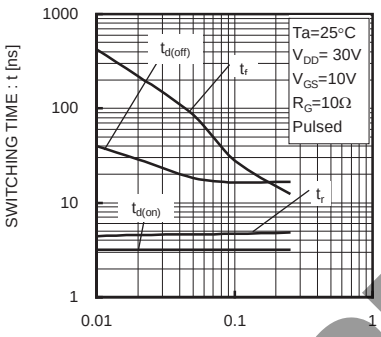


Fig.12 Switching Characteristics

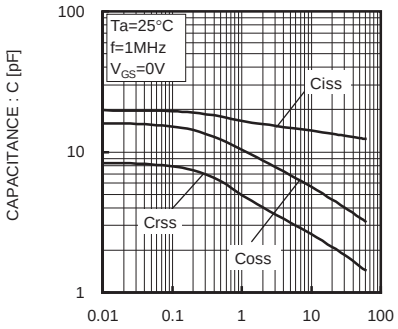


Fig.13 Typical Capacitance vs. Drain-Source Voltage

●**Measurement circuits**

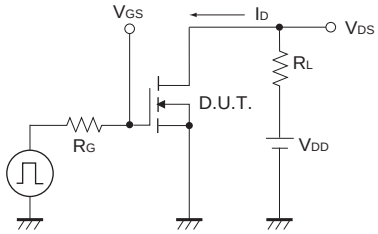


Fig.1-1 Switching time measurement circuit

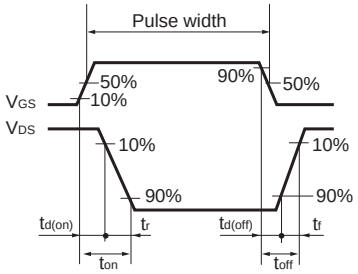


Fig.1-2 Switching waveforms

●**Notice**

This product might cause chip aging and breakdown under the large electrified environment.
Please consider to design ESD protection circuit.

Notes

No copying or reproduction of this document, in part or in whole, is permitted without the consent of ROHM Co.,Ltd.

The content specified herein is subject to change for improvement without notice.

The content specified herein is for the purpose of introducing ROHM's products (hereinafter "Products"). If you wish to use any such Product, please be sure to refer to the specifications, which can be obtained from ROHM upon request.

Examples of application circuits, circuit constants and any other information contained herein illustrate the standard usage and operations of the Products. The peripheral conditions must be taken into account when designing circuits for mass production.

Great care was taken in ensuring the accuracy of the information specified in this document. However, should you incur any damage arising from any inaccuracy or misprint of such information, ROHM shall bear no responsibility for such damage.

The technical information specified herein is intended only to show the typical functions of and examples of application circuits for the Products. ROHM does not grant you, explicitly or implicitly, any license to use or exercise intellectual property or other rights held by ROHM and other parties. ROHM shall bear no responsibility whatsoever for any dispute arising from the use of such technical information.

The Products specified in this document are intended to be used with general-use electronic equipment or devices (such as audio visual equipment, office-automation equipment, communication devices, electronic appliances and amusement devices).

The Products specified in this document are not designed to be radiation tolerant.

While ROHM always makes efforts to enhance the quality and reliability of its Products, a Product may fail or malfunction for a variety of reasons.

Please be sure to implement in your equipment using the Products safety measures to guard against the possibility of physical injury, fire or any other damage caused in the event of the failure of any Product, such as derating, redundancy, fire control and fail-safe designs. ROHM shall bear no responsibility whatsoever for your use of any Product outside of the prescribed scope or not in accordance with the instruction manual.

The Products are not designed or manufactured to be used with any equipment, device or system which requires an extremely high level of reliability the failure or malfunction of which may result in a direct threat to human life or create a risk of human injury (such as a medical instrument, transportation equipment, aerospace machinery, nuclear-reactor controller, fuel-controller or other safety device). ROHM shall bear no responsibility in any way for use of any of the Products for the above special purposes. If a Product is intended to be used for any such special purpose, please contact a ROHM sales representative before purchasing.

If you intend to export or ship overseas any Product or technology specified herein that may be controlled under the Foreign Exchange and the Foreign Trade Law, you will be required to obtain a license or permit under the Law.

ROHM SEMICONDUCTOR

Thank you for your accessing to ROHM product informations.
More detail product informations and catalogs are available, please contact us.

ROHM Customer Support System

http://www.rohm.com/contact/

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET ***category:***

Click to view products by ROHM ***manufacturer:***

Other Similar products are found below :

614233C 648584F IRFD120 JANTX2N5237 FCA20N60_F109 FDZ595PZ 2SK2545(Q,T) 405094E 423220D TPCC8103,L1Q(CM MIC4420CM-TR VN1206L SBVS138LT1G 614234A 715780A NTNS3166NZT5G SSM6J414TU,LF(T 751625C BUK954R8-60E NTE6400 SQJ402EP-T1-GE3 2SK2614(TE16L1,Q) 2N7002KW-FAI DMN1017UCP3-7 EFC2J004NUZTDG ECH8691-TL-W FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE221 NTE2384 NTE2903 NTE2941 NTE2945 NTE2946 NTE2960 NTE2967 NTE2969 NTE2976 NTE455 NTE6400A NTE2910 NTE2916 NTE2956 NTE2911 DMN2080UCB4-7 TK10A80W,S4X(S SSM6P69NU,LF DMP22D4UFO-7B DMN1006UCA6-7